

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



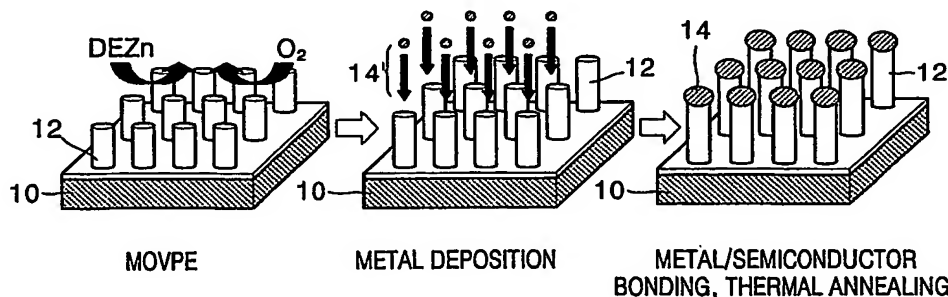
(43) International Publication Date
16 December 2004 (16.12.2004)

PCT

(10) International Publication Number
WO 2004/109815 A1

- (51) International Patent Classification⁷: **H01L 33/00**, (74) Agent: LEE, Young-Pil; The Cheonghwa Bldg., 1571-18 Seocho-dong, Seocho-gu, Seoul 137-874 (KR).
B82B 3/00
- (21) International Application Number: PCT/KR2004/000374
- (22) International Filing Date: 24 February 2004 (24.02.2004)
- (25) Filing Language: Korean
- (26) Publication Language: English
- (30) Priority Data:
10-2003-0036740 9 June 2003 (09.06.2003) KR
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).
- Published:
— with international search report
- For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: CONTACTS FABRIC USING HETEROSTRUCTURE OF METAL/SEMICONDUCTOR NANORODS AND FABRICATION METHOD THEREOF



(57) Abstract: Provided are a contact fabric using a heterostructure of metal/semiconductor nanorods and a method of manufacturing the same. An ohmic contact fabric having a low contact resistance or a Schottky contact fabric having a rectification characteristic is formed by selectively depositing metal of nano-sizes onto predetermined portions of zinc oxide/semiconductor nanorods and controlling the work function of the deposited metal and the interfacial characteristics of metal/zinc oxide. The contact fabric can be applied to various nano-sized electronic devices, including Schottky diodes, optical devices, and arrays thereof.